

IN THE CLAIMS:

Claims 1 - 7 (canceled)

8. (currently amended) A method of manufacturing a semiconductor integrated circuit device, comprising:

forming a first transistor of a MIS depletion type and a second transistor forming part of a masked ROM on a single semiconductor substrate by:

forming a well region of a first-conductivity-type in a first region where the first transistor is to be formed and a second region where the second transistor is to be formed;

~~selectively oxidizing the regions where the first and second transistors are to be formed;~~

implanting impurity ions of a first-conductivity-type in the regions where the first and second transistors are to be formed;

implanting impurity ions of a second-conductivity-type in the regions where the first and second transistors are to be formed to permit current to flow when a gate-source voltage of the first transistor is zero; and

forming a gate insulating film, a gate electrode, and source and drain regions of a second-conductivity-type in each of the first and second transistors.

9. (new) A method of manufacturing a semiconductor integrated circuit device, as claimed in claim 8, further comprising:

selectively forming a field oxide on the well region, wherein the field oxide separates the regions in which the first and second transistors are formed.